

Ultra fast Rectifier

IDP08E65D2

FEATURES

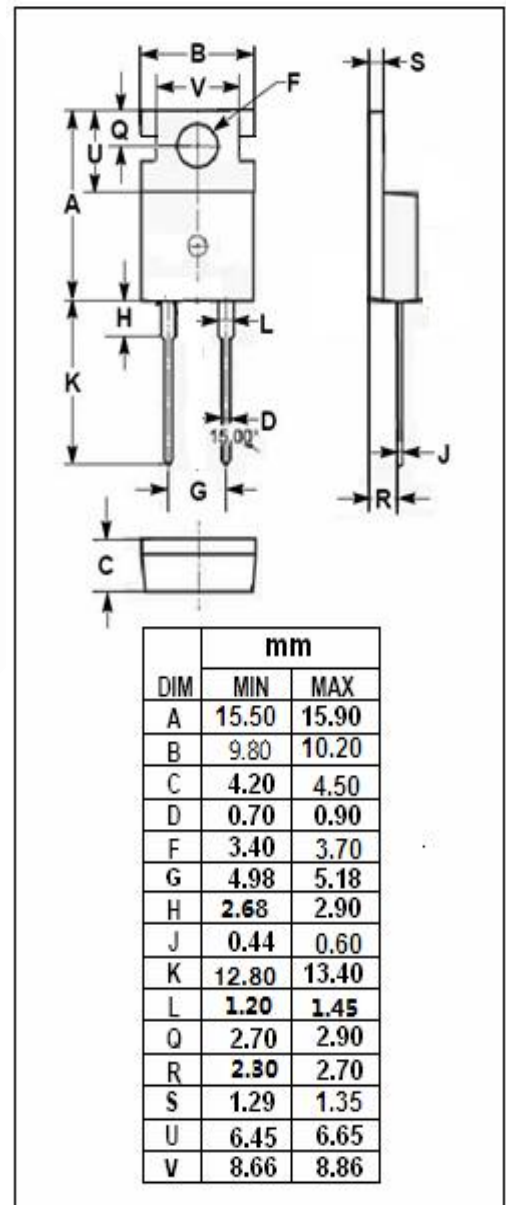
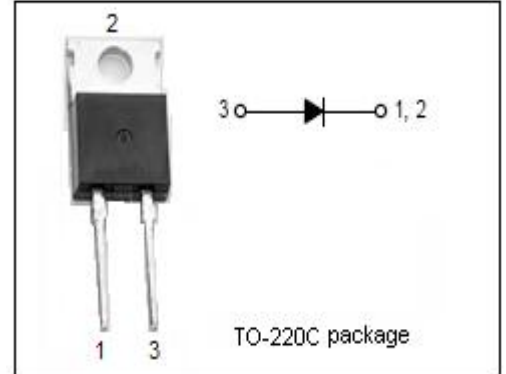
- With TO-220 packaging
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- Guardring for overvoltage protection
- High surge capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Switching power supply
- High frequency inverters
- Reverse battery protection
- Polarity protection applications

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{RRM} V _{RMS} V _R	Peak Repetitive Reverse Voltage RMS Voltage DC Blocking Voltage	650	V
I _{F(AV)}	Average Rectified Forward Current @T _c =25°C T _c =100°C	16 8	A
I _{FRM}	Repetitive Peak Surge Current (Square Wave)	24	A
I _{FSM}	Nonrepetitive Peak Surge Current 8.3 ms single half sine-wave superimposed on rated load conditions;One shot	64	A
P _D	Maximum Power Dissipation	56	W
T _j	Junction Temperature	-40~150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.69	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 μ s, Duty Cycle \leq 1%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	$I_F = 8A$	1.7	V
I_R	Maximum Instantaneous Reverse Current	$V_R = \text{rated } V_{RRM}; T_c = 25^{\circ}C$ $T_c = 175^{\circ}C$	40 2000	μA
t_{rr}	Maximum Reverse Recovery Time	$I_F = 8A; di_F/dt = 1000A/\mu s; V_R = 400V$	23	ns